

SPS

KA5L0380R

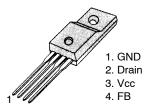
The SPS product family is specially designed for an off-line SMPS with minimal external components. The SPS consist of high voltage power SENSEFET[®] and current mode PWM IC.

Included PWM controller features integrated fixed frequency oscillator, under voltage lock—out, leading edge blanking, optimized gate turn—on/turn—off driver, thermal shutdown protection, over voltage protection, and temperature compensated precision current sources for loop compensation and fault protection circuitry. Compared to discrete MOSFET and PWM controller or RCC solution, a SPS can reduce total component count, design size, weight and at the same time increase efficiency, productivity, and system reliability.

It has a basic platform well suited for cost–effective design in either a flyback converter or a forward converter.

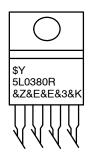
Features

- Precision Fixed Operating Frequency (50 kHz)
- Low Start-Up Current (Typ. 100 mA)
- Pulse By Pulse Current Limiting
- Over Current Protection
- Over Voltage Protection (Min. 25 V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Auto-Restart Mode
- This is a Pb-Free Device



TO-220F-4L CASE 340BK

MARKING DIAGRAM



\$Y = **onsemi** Logo

5L0380R = Specific Device Code &Z = Assembly Plant Code &E = Designates Space &3 = 3-Digit Date Code &K = Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

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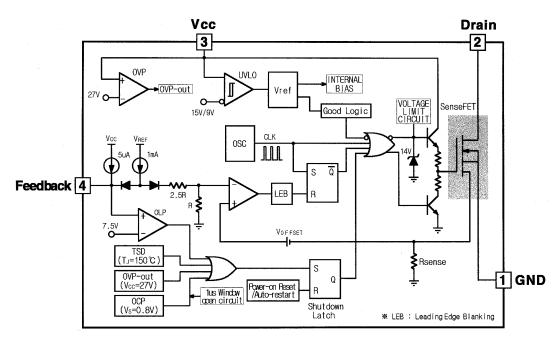


Figure 1. Block Diagram

ABSOLUTE MAXIMUM RATINGS

Rating	Symbo	ol Value	Unit
Drain-Source (GND) Voltage (Note 1)	V _{DSS}	800	V
Drain-Gate Voltage ($R_{GS} = 1 M\Omega$)	V_{DGF}	800	V
Gate-Source (GND) Voltage	V _{GS}	±30	V
Drain Current Pulsed (Note 2)	I _{DM}	12	A _{DC}
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	95	mJ
Avalanche Current (Note 4)	I _{AS}	-	Α
Continuous Drain Current (T _C = 25°C)	I _D	3.0	A _{DC}
Continuous Drain Current (T _C = 100°C)	I _D	2.1	A _{DC}
Supply Voltage	V _{CC}	30	V
Analog Input Voltage Range	V _{FB}	-0.3 to V _{SD}	V
Total Power Dissipation	P _D (wt H	I/S) 35	W
	Deratir	ng 0.28	W/°C
Operating Temperature	T _{OPR}	-25 to +85	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tj = 25° C to 150° C
- 2. Repetitive rating: Pulse width limited by maximum junction temperature.
- L = 51 mH, starting Tj = 25°C
 L = 13 μH, starting Tj = 25°C

ELECTRICAL CHARACTERISTICS (SFET PART) (T_a = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 50 \mu\text{A}$	800	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = Max., Rating, V _{GS} = 0 V	-	-	250	μΑ
		V _{DS} = 0.8 Max., Rating, V _{GS} = 0 V, T _C = 125°C	-	-	1000	μΑ
Static Drain–Source On Resistance (Note 5)	R _{DS(ON)}	V _{GS} = 10 V, I _D = 0.5 A	-	4	5	Ω
Forward Transconductance (Note 5)	gfs	$V_{DS} = 50 \text{ V}, I_{D} = 0.5 \text{ A}$	1.5	2.5	-	S
Input Capacitance	Ciss	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	779	-	pF
Output Capacitance	Coss		-	75.6	-	
Reverse Transfer Capacitance	Crss	1	-	24.9	-	
Turn Off Delay Time	td(on)	V _{DD} = 0.5 BV _{DSS} , I _D = 1.0 A	-	40	-	ns
Rise Time	tr	(MOSFET switching time are essentially independent	-	95	-	
Turn Off Delay Time	td(off)	of operating temperature)	-	150	-	
Fall Time	tf]	-	60	-	
Total Gate Charge (Gate-source + Gate-drain)	Qg	$V_{GS} = 10 \text{ V}, I_{D} = 1.0 \text{ A},$ $V_{DS} = 0.5 \text{ BV}_{DSS}$	-	-	34	nC
Gate-Source Charge	Qgs	(MOSFET switching time are essentially independent	-	7.2	-	
Gate-Drain (Miller) Charge	Qgd	of operating temperature)	_	12.1	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulse test: Pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.

ELECTRICAL CHARACTERISTICS (CONTROL PART) ($T_a = 25$ °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
REFERENCE SECTION	•		•	•		•
Output Voltage (Note 6)	Vref	T _a = 25°C	4.80	5.00	5.20	V
Temperature Stability (Note 6, Note 7)	Vref/∆T	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
OSCILLATOR SECTION	•		•	•		•
Initial Accuracy	Fosc	T _a = 25°C	45	50	55	kHz
Frequency Change with Temperature (Note 7)	ΔF/ΔΤ	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%
PWM SECTION						
Maximum Duty Cycle	Dmax	-	74	77	80	%
FEEDBACK SECTION						
Feedback Source Current	I _{FB}	$T_a = 25^{\circ}C$, 0 V \leq Vfb \leq 3 V	0.7	0.9	1.1	mA
Shutdown Delay Current	Idelay	$T_a = 25^{\circ}C$, 5 V \leq Vfb \leq V _{SD}	4	5	6	μΑ
OVER CURRENT PROTECTION SECTION	ON	•				
Over Current Protection	I _L (max)	Max. Inductor current	1.89	2.15	2.41	Α
UVLO SECTION		•				
Start Threshold Voltage	Vth(H)	-	8.4	9	9.6	V
Minimum Operating Voltage	Vth(L)	After turn on	14	15	16	V
TOTAL STANDBY CURRENT SECTION						
Start Current	I _{ST}	V _{CC} = 14 V	-	0.1	0.17	mA
Operating Supply Current (Control Part Only)	I _{OPR}	V _{CC} ≤ 28	-	7	12	mA
SHUTDOWN SECTION	•	•	•	•	•	•
Shutdown Feedback Voltage	V _{SD}	Vfb ≥ 6.5 V	6.9	7.5	8.1	V
Thermal Shutdown Temperature (Tj) (Note 6)	T _{SD}	-	140	160	-	°C
Over Voltage Protection	V _{OVP}	V _{CC} ≥ 24 V	25	27	29	V
			•			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. These parameters, although guaranteed, are not 100% tested in production.

7. These parameters, although guaranteed, are tested in EDS (wafer test) process.

TYPICAL PERFORMANCE CHARACTERISTICS (SFET part)

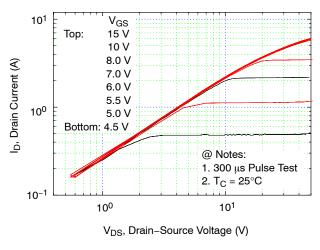


Figure 2. Output Characteristics

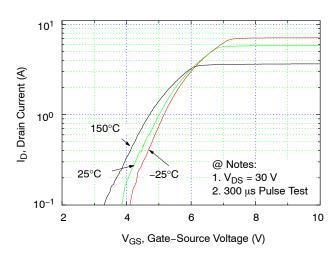


Figure 3. Transfer Characteristics

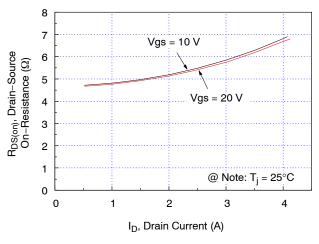


Figure 4. On-Resistance vs. Drain Current

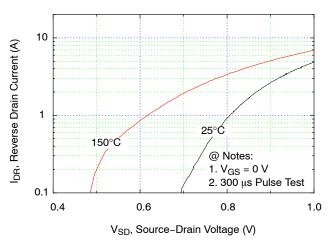


Figure 5. Source-Drain Diode Forward Voltage

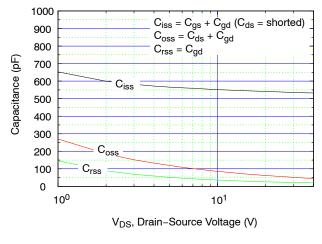


Figure 6. Capacitance vs. Drain-Source Voltage

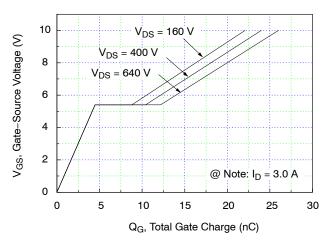
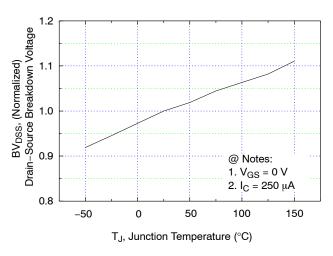


Figure 7. Gate Charge vs. Gate-Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (continued)



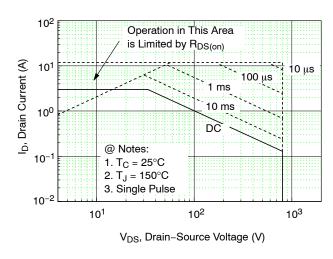
2.5

Source 2.0

(position of the properties of

Figure 8. Breakdown Voltage vs. Temperature

Figure 9. On-Resistance vs. Temperature



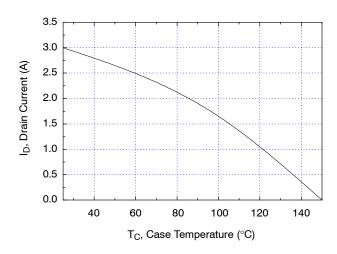


Figure 10. Max. Safe Operating Area

Figure 11. Max. Drain Current vs. Case Temperature

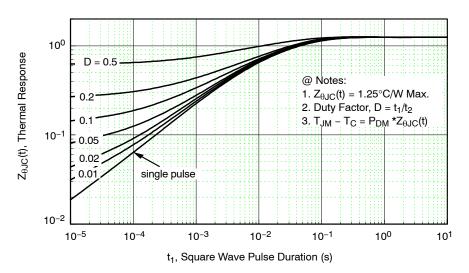


Figure 12. Thermal Response

TYPICAL PERFORMANCE CHARACTERISTICS (Control part)

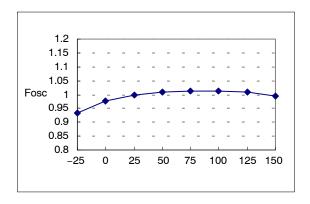


Figure 13. Operating Frequency

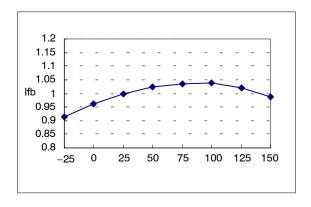


Figure 14. Feedback Source Current

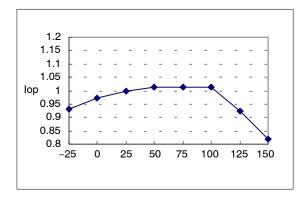


Figure 15. Operating Current

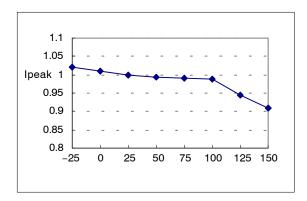


Figure 16. Max Inductor Current

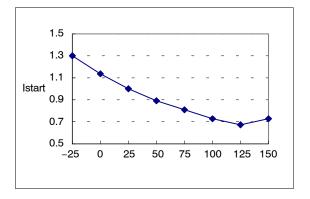


Figure 17. Start Up Current

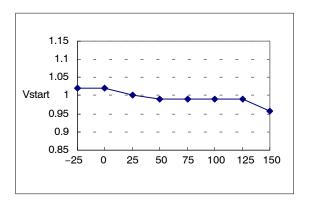


Figure 18. Start Threshold Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

(These characteristic graphs are normalized at $Ta = 25^{\circ}C$)

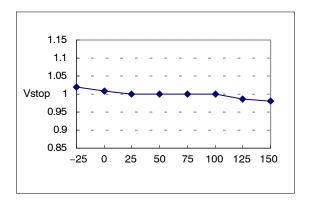


Figure 19. Stop Threshold Voltage

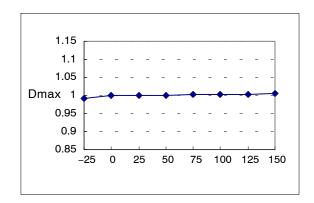


Figure 20. Maximum Duty Cycle

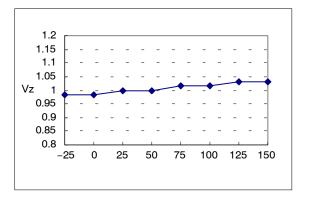


Figure 21. Vcc Zener Voltage

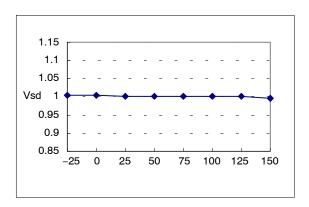


Figure 22. Shutdown Feedback Voltage

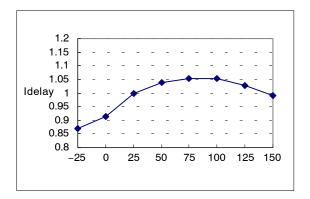


Figure 23. Shutdown Delay Current

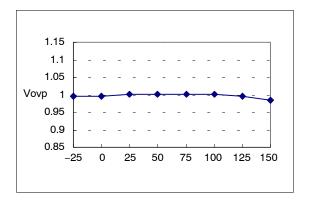
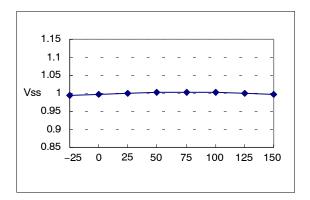


Figure 24. Over Voltage Protection

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

(These characteristic graphs are normalized at Ta = 25° C)



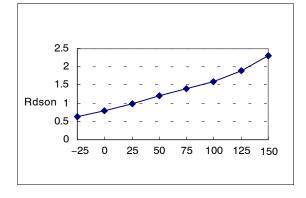


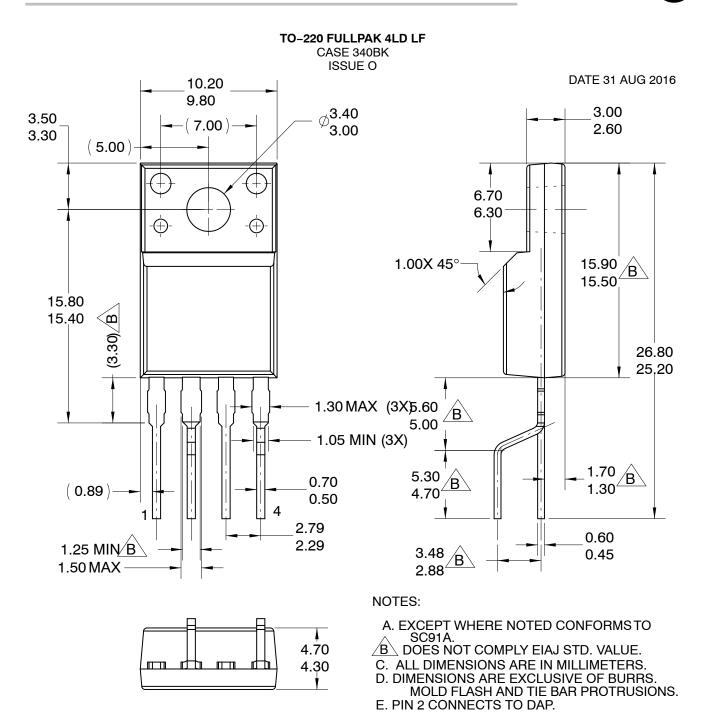
Figure 25. Soft Start Voltage

Figure 26. Drain Source Turn-On Resistance

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Packing Method
KA5L0380R	−25 to +85°C	TO-220F-4L (Pb-Free)	Tube

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